

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANTS

MAY 09 2002

ATTY. DOCKET NO.
P-4007-USAPPLICATION NO.
09/988,122APPLICANTS
Bloom et al.CONFIRMATION NO.
8188FILING DATE
11/19/01GROUP
2818

U.S. PATENT DOCUMENTS

EXAM. INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>AB</i>	3,895,360	07/15/1975	Cricchi et al.			
	4,016,588	04/05/1977	Ohya et al.			
	4,017,888	04/12/1977	Christie et al.			
	4,151,021	04/24/1979	McElroy			
	4,173,766	11/06/1979	Hayes			
	4,173,791	11/06/1979	Bell			
	4,257,832	03/24/1981	Schwabe et al.			
	4,306,353	12/22/1981	Jacobs et al.			
	4,342,149	08/03/1982	Jacobs et al.			
	4,360,900	11/23/1982	Bate			
	4,380,057	04/12/1983	Kotecha et al.			
	4,471,373	09/11/1984	Shimizu et al.			
	4,521,796	06/04/1985	Rajkanan et al.			
	4,527,257	07/02/1985	Cricchi			
	4,630,085	12/16/1986	Koyama			
	4,667,217	05/19/1987	Janning			
	4,742,491	05/03/1988	Liang et al.			
	4,769,340	09/06/1988	Chang et al.			
	4,780,424	10/25/1988	Holler et al.			
	4,847,808	07/11/1989	Kobatake			
	4,870,470	09/26/1989	Bass, Jr. et al.			
	4,941,028	07/10/1990	Chen et al.			
	5,021,999	06/04/1991	Kohda et al.			
	5,075,245	12/24/1991	Woo et al.			
	5,104,819	04/14/1992	Freiberger et al.			
	5,159,570	10/27/1992	Mitchell et al.			
	5,168,334	12/01/1992	Mitchell et al.			
	5,175,120	12/29/1992	Lee			
<i>AB</i>	5,214,303	05/25/1993	Aoki			

EXAMINER

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<i>MB</i>	5,305,262	04/19/1994	Yoneda			
	5,311,049	05/10/1994	Tsuruta			
	5,324,675	06/28/1994	Hayabuchi			
	5,338,954	08/16/1994	Shimoji			
	5,349,221	09/20/1994	Shimoji			
	5,350,710	09/27/1994	Hong et al.			
	5,359,554	10/25/1994	Odake et al.			
	5,393,701	02/28/1995	Ko et al.			
	5,394,355	02/28/1995	Uramoto et al.			
	5,414,693	05/09/1995	Ma et al.			
	5,418,176	05/23/1995	Yang et al.			
	5,418,743	05/23/1995	Tomioka et al.			
	5,422,844	06/06/1995	Wolstenholme et al.			
	5,424,567	06/13/1995	Chen			
	5,426,605	06/20/1995	Van Berkel et al.			
	5,434,825	07/18/1995	Harari			
	5,436,481	07/25/1995	Egawa et al.			
	5,455,793	10/03/1995	Amin et al.			
	5,467,308	11/14/1995	Chang et al.			
	5,477,499	12/19/1995	Van Buskirk et al.			
	5,496,753	03/05/1996	Sakurai et al.			
	5,518,942	05/21/1996	Shrivastava			
	5,523,251	06/04/1996	Hong			
	5,553,018	09/03/1996	Wang et al.			
	5,599,727	02/04/1997	Hakozaki et al.			
	5,654,568	08/05/1997	Nakao			
	5,656,513	08/12/1997	Wang et al.			
<i>MB</i>	5,712,814	01/27/1998	Fratin et al.			

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Richard A. Booth

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EXAM. INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AB	5,726,946	03/10/1998	Yamagata et al.	1		
	5,760,445	06/02/1998	Diaz			
	5,768,192	06/16/1998	Eitan			
	5,787,036	07/28/1998	Okazawa			
	5,793,079	08/11/1998	Georgescu et al.			
	5,801,076	09/01/1998	Ghneim et al.			
	5,812,449	09/22/1998	Song			
	5,825,686	10/20/1998	Schmitt-Landsiedel et al.			
	5,836,772	11/17/1998	Chang et al.			
	5,841,700	11/24/1998	Chang			
	5,847,441	12/08/1998	Cutter et al.			
	5,864,164	01/26/1999	Wen			
	5,870,335	02/09/1999	Khan et al.			
	5,903,031	05/11/1999	Yamada et al.			
	5,946,558	08/31/1999	Hsu			
	5,963,412	10/05/1999	En			
	5,973,373	10/26/1999	Krautschneider et al.			
	5,991,202	11/23/1999	Derhacobian et al.			
	6,011,725	01/04/2000	Eitan			
	6,018,186	01/25/2000	Hsu			
	6,020,241	02/01/2000	You et al.			
	6,028,324	02/22/2000	Su et al.			
	6,030,871	02/29/2000	Eitan			
	6,034,403	03/07/2000	Wu			
	6,034,896	03/07/2000	Ranaweera et al.			
	6,063,666	05/16/2000	Chang et al.			
	6,201,282	03/13/2001	Eitan			
AB	08/902,890	07/30/1997	Eitan			

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<i>AB</i>	08/905,286	07/30/1997	Eitan	—	—	
	09/348,720	07/06/1999	Eitan	—	—	
	09/413,408	10/06/1999	Eitan	—	—	
<i>AB</i>	09/536,125	03/28/2000	Eitan et al.	—	—	

EXAMINER

A handwritten signature in dark ink, appearing to read "Richard A. R.".

DATE CONSIDERED

A handwritten date "1/13/03" in dark ink.

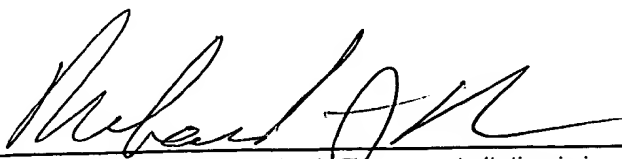
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	EP 0751560	01/02/1997	Europe				
	EP 1073120	01/31/2001	Europe				
	GB 1297899	11/29/1972	Great Britn				
	GB 2157489	10/23/1985	Great Britn				
	JP 05021758	01/29/1993	Japan				
	JP 07193151	07/28/1995	Japan				
	JP 09162314	06/20/1997	PCT				
	WO 81/00790	03/19/1981	PLT				
	WO 96/25741	08/22/1996	PCT				

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
<i>MS</i>	Chan et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <u>IEEE Electron Device Letters</u> , Vol. EDL-8, No. 3, March, 1987.
	Chang, J., "Non Volatile Semiconductor Memory Devices," <u>Proceedings of the IEEE</u> , Volume 64 No. 7, pp. 1039-1059, July, 1976.
	Eitan et al., "Hot-Electron Injection into the Oxide in n-Channel MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. ED-28, No. 3, pp.328-340, March 1981.
	Glasser et al., "The Design and Analysis of VLSI Circuits," Addison Wesley Publishing Co, Chapter 2, 1988.
	Lee, H., "A New Approach For the Floating-Gate MOS NonVolatile Memory", <u>Applied Physics Letters</u> , Vol. 31, No. 7, pages 475-6, October 1977.
	Ma et al., "A dual-bit Split-Gate EEPROM (DSG) Cell in Contactless Array for Single-Vcc High Density Flash Memories," <u>IEEE</u> , pp. 3.5.1-3.5.4, 1994.
	Ohshima et al., "Process and Device Technologies for 16Mbit Eproms with Large - Tilt - Angle implanted P-Pocket Cell," <u>IEEE</u> , CH2865-4/90/0000-0095, pp. 5.2.1 - 5.2.4, December, 1990.
	Ricco, Bruno et al., "Nonvolatile Multilevel Memories for Digital Application," <u>IEEE</u> , Vol. 86, No 12, pages 2399-2421, December, 1998.
	Roy, Anirban "Characterization and Modeling of Charge Trapping and Retention in Novel Multi-Dielectric Nonvolatile Semiconductor Memory Devices," Doctoral Dissertation, Sherman Fairchild Center, Department of Computer Science and Electrical Engineering, pp. 1-35, 1989.
	"2 Bit/Cell EEPROM Cell Using Band-To-Band Tunneling For Data Read-Out," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. NY Vol. 35, No. 4B, ISSN:0018-8689, September, 1992.
	Tseng, Hsing-Huang et al., "Thin CVD Stacked Gate Dielectric for ULSI Technology", <u>IEEE</u> , 0-7803-1450-6, 1993.
	Pickar, K.A., "Ion Implantation in Silicon," <u>Applied Solid State Science</u> , Vol. 5, R. Wolfe Edition, Academic Press, New York, 1975.
	Bhattacharyya et al., "FET Gate Structure for Nonvolatile N-Channel Read-Mostly Memory Device," <u>IBM Technical Disclosure Bulletin</u> , U.S. IBM Corp. Volume 18, No. 6, page 1768, November, 1975.
	Bude et al., "EEPROM/Flash Sub 3.0 V Drain-Source Bias Hot carrier Writing", <u>IEDM 95</u> , pp. 989-992.
	Bude et al., "Secondary Electron Flash - a High Performance, Low Power Flash Technology for 0.35 um and Below", <u>IEDM 97</u> , pp. 279-282.
<i>MS</i>	Bude et al., "Modeling Nonequilibrium Hot Carrier Device Effects", <u>Conference of Insulator Specialists of Europe</u> , Sweden, June, 1997.

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